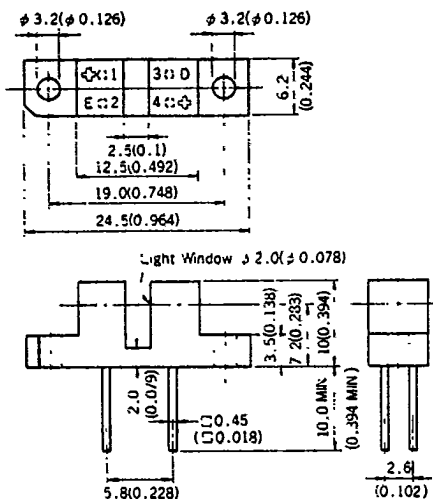


# PHOTO INTERRUPTER PS4008

## PHOTO INTERRUPTER

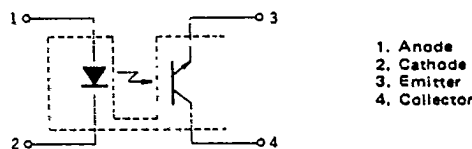
### PACKAGE DIMENSIONS in millimeters (inches)



### DESCRIPTION

The PS4008 photo coupled interrupter module containing a GaAs light emitting diode and an NPN silicon photo-transistor.

### CONNECTION DIAGRAM (Top View)



- 1. Anode
- 2. Cathode
- 3. Emitter
- 4. Collector

### ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

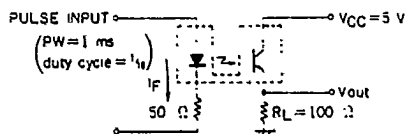
#### Diode

Reverse Voltage	$V_R$	5.0	V
Forward Current	$I_F$	50	mA
Power Dissipation	$P_D$	100	mW

#### Transistor

Collector to Emitter Voltage	$V_{CE0}$	30	V
Collector Current	$I_C$	40	mA
Power Dissipation	$P_C$	100	mW
Storage Temperature	$T_{stg}$	-40 to +100	°C
Operating Temperature	$T_{opt}$	-20 to +80	°C

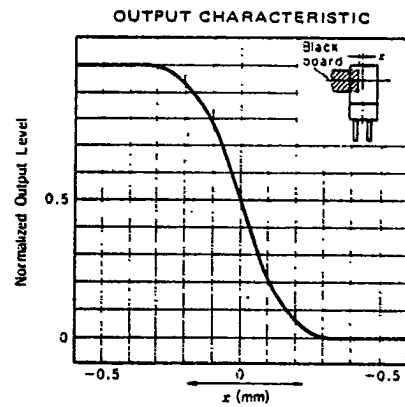
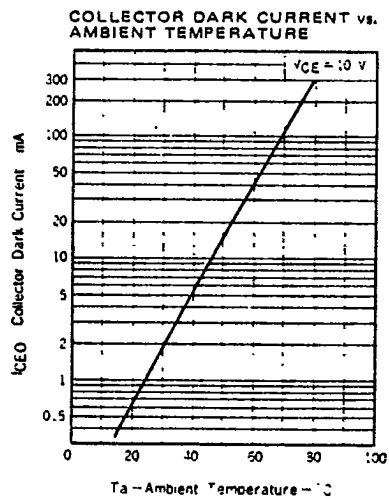
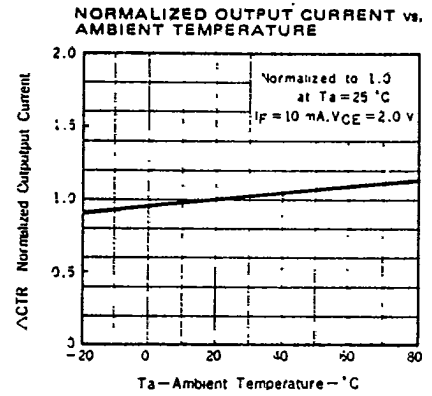
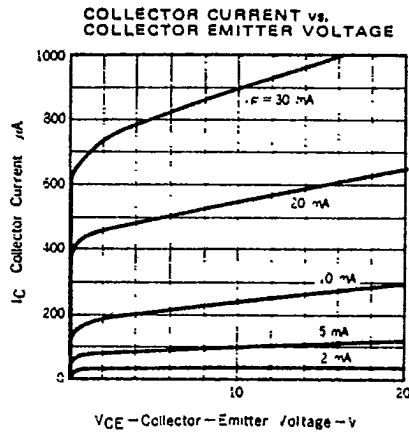
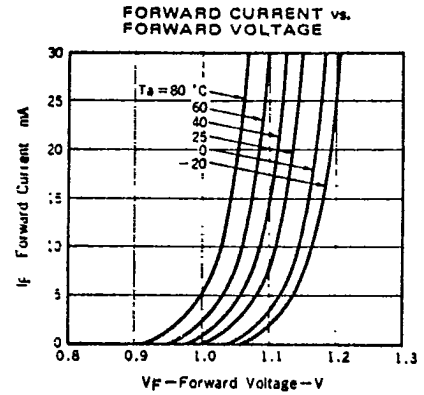
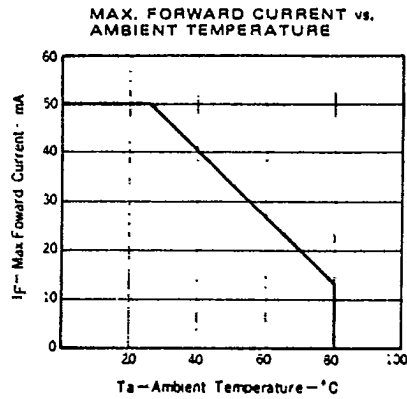
### \*Test Circuit for Switching Time



### ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

	CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Diode	Forward Voltage	$V_F$		1.1	1.4	V	$I_F = 20 \text{ mA}$
	Reverse Current	$I_R$			20	$\mu\text{A}$	$V_R = 4.0 \text{ V}$
	Junction Capacitance	C		100		pF	$V = 0, f = 1.0 \text{ MHz}$
Transistor	Collector to Emitter Dark Current	$I_{CE0}$			100	nA	$V_{CE} = 10 \text{ V}, I_F = 0$
Coupled	Output Current	$I_C$	50	200		$\mu\text{A}$	$I_F = 10 \text{ mA}, V_{CE} = 2.0 \text{ V}$
	Collector Saturation Voltage	$V_{CE(sat)}$			0.3	V	$I_F = 10 \text{ mA}, I_C = 50 \mu\text{A}$
	Rise Time	$t_r$		5		$\mu\text{s}$	$V_{CC} = 5.0 \text{ V}, I_C = 50 \mu\text{A}, R_L = 100 \Omega$
	Fall Time	$t_f$		5		$\mu\text{s}$	$V_{CC} = 5.0 \text{ V}, I_C = 50 \mu\text{A}, R_L = 100 \Omega$

TYPICAL CHARACTERISTICS (Ta = 25 °C)



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